(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
5 October 2006 (05.10.2006)

PCT

(10) International Publication Number
WO 2006/104634 A3

(51) International Patent Classification:
H01L 21/311 (2006.01) *H01L 21/033* (2006.01)

(21) International Application Number:
PCT/US2006/007333

(22) International Filing Date:
27 February 2006 (27.02.2006)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/666,031 28 March 2005 (28.03.2005) US
11/216,477 31 August 2005 (31.08.2005) US

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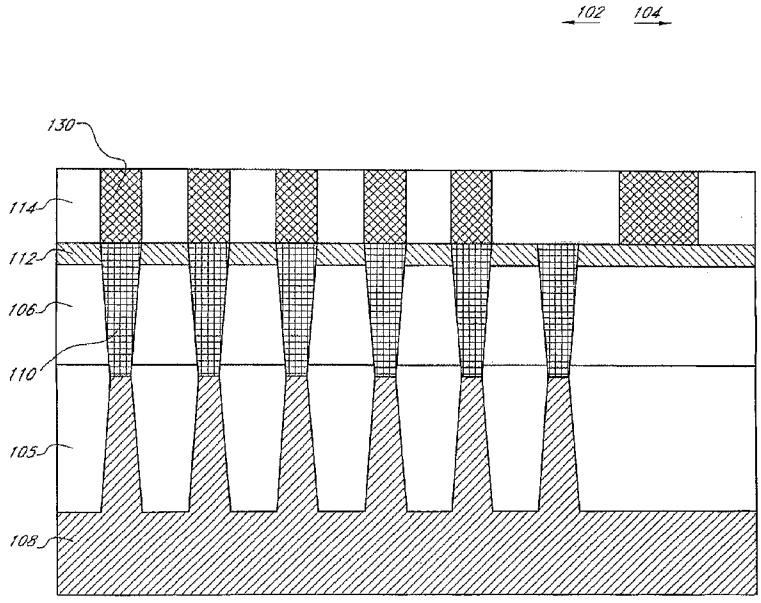
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

[Continued on next page]

(54) Title: INTEGRATED CIRCUIT FABRICATION



(57) Abstract: A method for defining patterns in an integrated circuit (100) comprises defining a plurality of features in a first photoresist layer using photolithography over a first region (102) of a substrate (108). The method further comprises using pitch multiplication to produce at least two features (120) in a lower masking layer (116) for each feature in the photoresist layer. The features in the lower masking layer (116) include looped ends (124). The method further comprises covering with a second photoresist layer (126) a second region (104) of the substrate (108) including the looped ends (124) in the lower masking layer (116). The method further comprises etching a pattern of trenches in the substrate (108) through the features in the lower masking layer without etching in the second region (104). The trenches have a trench width.

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— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
8 March 2007

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.